Unit: mm

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSVI)

2SK3562

Switching Regulator Applications

• Low drain-source ON resistance: RDS (ON) = 0.9Ω (typ.)

• High forward transfer admittance: $|Y_{fs}| = 5.0S$ (typ.)

• Low leakage current: IDSS = 100 $\,\mu$ A (VDS = 600 V)

• Enhancement mode: $V_{th} = 2.0 \sim 4.0 \text{ V (V}_{DS} = 10 \text{ V, I}_{D} = 1 \text{ mA})$

Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V_{DSS}	600	V	
Drain-gate voltage (F	$R_{GS} = 20 \text{ k}\Omega$)	V_{DGR}	600	V	
Gate-source voltage		V _{GSS}	±30	V	
Drain current	DC (Note 1)	ID	6	А	
	Pulse (t = 1 ms) (Note 1)	I _{DP}	24		
Drain power dissipati	on (Tc = 25°C)	P _D	40	W	
Single pulse avalanche energy (Note 2)		E _{AS}	345	mJ	
Avalanche current		I _{AR}	6	Α	
Repetitive avalanche energy (Note 3)		E _{AR}	4	mJ	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	

1: Gate 2: Drain 3: Source

SC-67

2-10U1B

Weight: 1.7 g (typ.)

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Thermal Characteristics

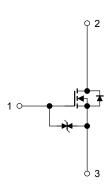
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch-c)}	3.125	°C/W
Thermal resistance, channel to ambient	R _{th (ch-a)}	62.5	°C/W

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V_{DD} = 90 V, T_{ch} = 25°C(initial), L = 16.8 mH, I_{AR} = 6 A, R_G = 25 Ω

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Please handle with caution.



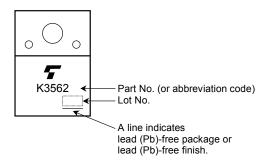
Electrical Characteristics (Ta = 25°C)

Chara	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cur	rent	I _{GSS}	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±10	μΑ
Gate-source brea	kdown voltage	V (BR) GSS	$I_G = \pm 10 \ \mu A, \ V_{DS} = 0 \ V$	±30	_	_	V
Drain cut-off curre	ent	I _{DSS}	V _{DS} = 600 V, V _{GS} = 0 V		_	100	μΑ
Drain-source brea	akdown voltage	V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	600	_	_	V
Gate threshold vo	oltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	2.0	_	4.0	V
Drain-source ON	resistance	R _{DS (ON)}	V _{GS} = 10 V, I _D = 3 A		0.9	1.25	Ω
Forward transfer	admittance	Y _{fs}	V _{DS} = 10 V, I _D = 3 A	1.2	5.0	_	S
Input capacitance		C _{iss}	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz		1050	_	pF
Reverse transfer capacitance		C _{rss}		_	10	_	
Output capacitance		C _{oss}			110	_	
Switching time	Rise time	t _r	V_{GS} $V_{DD} \simeq 200 \text{ V}$	_	20	_	
	Turn-on time	t _{on}		_	40	_	
	Fall time	t _f		_	35	_	ns
	Turn-off time	t _{off}	Duty \leq 1%, $t_W = 10 \ \mu s$	_	130		
Total gate charge		Qg		_	28	_	
Gate-source charge		Q _{gs}	$V_{DD} \simeq 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 6 \text{ A}$	_	16	_	nC
Gate-drain charge		Q _{gd}		_	12	_	

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	_	_	_	6	А
Pulse drain reverse current (Note 1)	I _{DRP}	_	_	_	24	Α
Forward voltage (diode)	V _{DSF}	I _{DR} = 6 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	t _{rr}	$I_{DR} = 6 \text{ A}, V_{GS} = 0 \text{ V},$	_	1000	_	ns
Reverse recovery charge	Q _{rr}	dI _{DR} /dt = 100 A/μs	_	7.0	_	μС

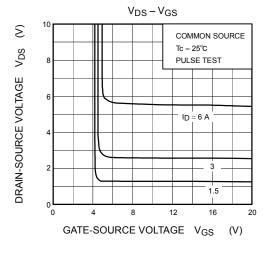
Marking

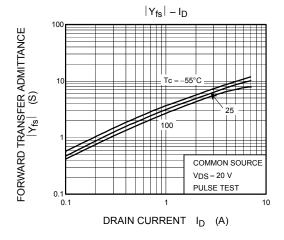


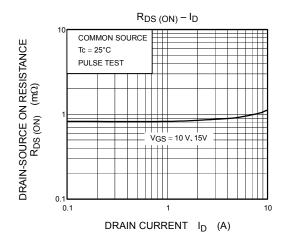
TD - VDS

TO - V

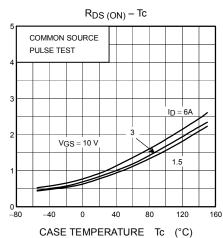
EVEN TO SERVICE VOLTAGE VGS (V)

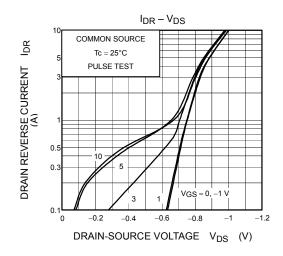


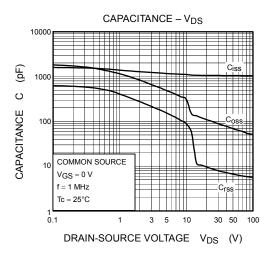


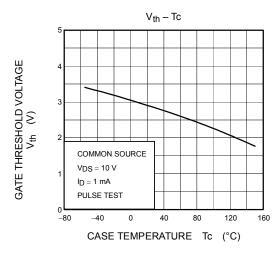


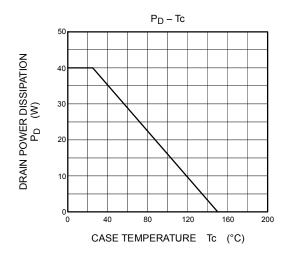


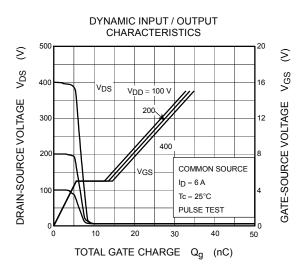


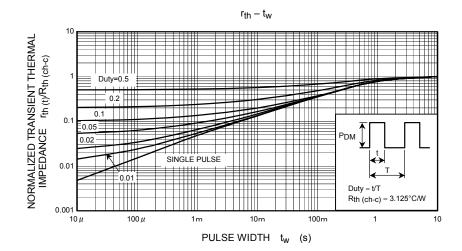




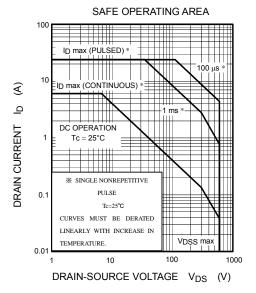


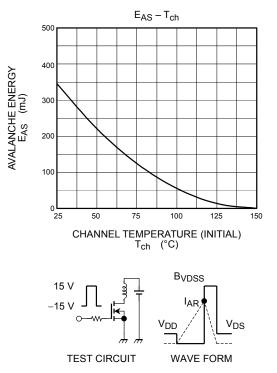






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$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{BVDSS}{BVDSS - VDD} \right)$$

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